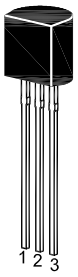
2SA1505

PNP Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into two groups, O and Y, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	35	V
Collector Emitter Voltage	$-V_{CEO}$	30	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	500	mA
Base Current	$-I_B$	50	mA
Power Dissipation	P_{tot}	150	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

Characteristics at T_a = 25 °C

Parameter			Symbol	Min.	Typ.	Max.	Unit
DC Current Gain							
at $-V_{CE}$ = 1 V, $-I_C$ = 100 mA	Current Gain Group	O	h_{FE}	70	-	140	-
		Y	h_{FE}	120	-	240	-
at $-V_{CE}$ = 6 V, $-I_C$ = 400 mA		O	h_{FE}	25	-	-	-
		Y	h_{FE}	40	-	-	-
Collector Base Cutoff Current at $-V_{CB}$ = 35 V			$-I_{CBO}$	-	-	0.1	µA
Emitter Base Cutoff Current at $-V_{EB}$ = 5 V			$-I_{EBO}$	-	-	0.1	µA
Collector Emitter Saturation Voltage at $-I_C$ = 100 mA, $-I_B$ = 10 mA			$-V_{CE(sat)}$	-	0.1	0.25	V
Base Emitter Voltage at $-V_{CE}$ = 1 V, $-I_C$ = 100 mA			$-V_{BE}$	-	0.8	1	V
Gain Bandwidth Product at $-V_{CE}$ = 6 V, $-I_C$ = 20 mA			f_T	-	200	-	MHz
Output Capacitance at $-V_{CB}$ = 6 V, f = 1 MHz			C_{ob}	-	13	-	pF